

In the Claims:

Please amend claims 14 and 19 pursuant to 37 CFR 1.121(c)(1)(i) as set forth in the "clean" version set forth below. A version with markings to show the changes made pursuant to 37 CFR 1.121(c)(1)(ii) is attached hereto as Appendix A.

B1 *subc1* →

14. (Amended) A semiconductor device comprising:
a semiconductor substrate;
a MOS type transistor formed on said semiconductor substrate, said MOS type transistor including a source, a gate and a drain;
an interlayer insulating film formed on the semiconductor substrate, said interlayer insulating film covering said MOS type transistor and including a hydrogen resident film;
a wiring layer formed on said interlayer insulating film; and
a hydrogen transmission preventing film covering said MOS type transistor and said wiring layer, said hydrogen transmission preventing film is a silicon oxide film contains a SI-H residue of 61% or less.

B2 *subc1* →

19. (Amended) A semiconductor device comprising:
a semiconductor substrate;
a MOS type transistor formed on said semiconductor substrate, said MOS type transistor including a source, a gate and a drain;
an interlayer insulating film formed on the semiconductor substrate, said interlayer insulating film covering said MOS type transistor and including a hydrogen resident film;
a wiring layer formed on said interlayer insulating film, wherein said wiring layer includes a plurality of adjacent wiring layers; and

B2
cont

a hydrogen transmission preventing film covering said MOS type transistor and said wiring layer, and wherein said hydrogen transmission preventing film forms an air filled groove between adjacent wiring layers.
